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This document, MC74HC4066/D has been canceled and replaced by MC74HC4066A/D LAN was sent 9/28/01

Quad Analog Switch/ Multiplexer/Demultiplexer

High-Performance Silicon-Gate CMOS

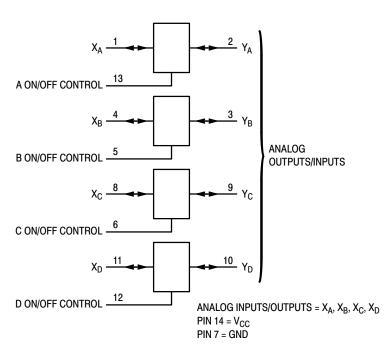
The MC54/74HC4066 utilizes silicon–gate CMOS technology to achieve fast propagation delays, low ON resistances, and low OFF–channel leakage current. This bilateral switch/multiplexer/demultiplexer controls analog and digital voltages that may vary across the full power–supply range (from $\rm V_{CC}$ to GND).

The HC4066 is identical in pinout to the metal–gate CMOS MC14016 and MC14066. Each device has four independent switches. The device has been designed so that the ON resistances (R_{ON}) are much more linear over input voltage than R_{ON} of metal–gate CMOS analog switches.

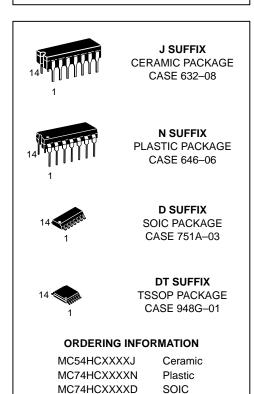
This device is identical in both function and pinout to the HC4016. The ON/OFF control inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs. For analog switches with voltage–level translators, see the HC4316.

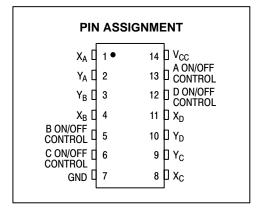
- · Fast Switching and Propagation Speeds
- High ON/OFF Output Voltage Ratio
- Low Crosstalk Between Switches
- Diode Protection on All Inputs/Outputs
- Wide Power–Supply Voltage Range (V_{CC} GND) = 2.0 to 12.0 Volts
- Analog Input Voltage Range (V_{CC} GND) = 2.0 to 12.0 Volts
- Improved Linearity and Lower ON Resistance over Input Voltage than the MC14016 or MC14066 or HC4016
- Low Noise
- Chip Complexity: 44 FETs or 11 Equivalent Gates

LOGIC DIAGRAM



MC54/74HC4066





TSSOP

MC74HCXXXXDT

MAXIMUM RATINGS*

| Symbol | Parameter | Value | Unit |
|------------------|--|--------------------------------|------|
| V _{CC} | Positive DC Supply Voltage (Referenced to GND) | - 0.5 to + 14.0 | V |
| V _{IS} | Analog Input Voltage (Referenced to GND) | -0.5 to $V_{CC} + 0.5$ | V |
| V _{in} | Digital Input Voltage (Referenced to GND) | - 1.5 to V _{CC} + 1.5 | V |
| I | DC Current Into or Out of Any Pin | ± 25 | mA |
| P _D | Power Dissipation in Still Air, Plastic or Ceramic DIP† SOIC Package† TSSOP Package† | 750 500 450 | mW |
| T _{stg} | Storage Temperature | - 65 to + 150 | °C |
| TL | Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC or TSSOP Package) (Ceramic DIP) | 260 300 | °C |

^{*} Maximum Ratings are those values beyond which damage to the device may occur. Functional operation should be restricted to the Recommended Operating Conditions.

†Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C Ceramic DIP: – 10 mW/°C from 100° to 125°C SOIC Package: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter | | | Max | Unit |
|---------------------------------|---|-------------------------|-----|-----------------|------|
| V _{CC} | Positive DC Supply Voltage (Referenced to G | ND) | 2.0 | 12.0 | V |
| V _{IS} | Analog Input Voltage (Referenced to GND) | | | V_{CC} | V |
| V _{in} | Digital Input Voltage (Referenced to GND) | | | V _{CC} | V |
| V _{IO} * | Static or Dynamic Voltage Across Switch | | | 1.2 | V |
| T _A | Operating Temperature, All Package Types | | | + 125 | °C |
| t _r , t _f | Input Rise and Fall Time, ON/OFF Control | | | | ns |
| | Inputs (Figure 10) | $_{CC} = 2.0 \text{ V}$ | 0 | 1000 | |
| | V | CC = 4.5 V | 0 | 500 | |
| | V | $_{CC} = 9.0 \text{ V}$ | 0 | 400 | |
| | V _C | _C = 12.0 V | 0 | 250 | |

^{*} For voltage drops across the switch greater than 1.2 V (switch on), excessive V_{CC} current may be drawn; i.e., the current out of the switch may contain both V_{CC} and switch input components. The reliability of the device will be unaffected unless the Maximum Ratings are exceeded.

DC ELECTRICAL CHARACTERISTIC Digital Section (Voltages Referenced to GND)

| | | | | Guaranteed Limit | | | |
|-----------------|---|--|---------------------------|---------------------------|---------------------------|---------------------------|------|
| Symbol | Parameter | Test Conditions | V _{CC} V | – 55 to 25°C | ≤ 85°C | ≤ 125°C | Unit |
| V _{IH} | Minimum High–Level Voltage ON/OFF Control Inputs | R _{on} = Per Spec | 2.0 4.5 9.0 12.0 | 1.5 3.15 6.3 8.4 | 1.5 3.15 6.3 8.4 | 1.5 3.15 6.3 8.4 | V |
| V _{IL} | Maximum Low–Level Voltage ON/OFF Control Inputs | R _{on} = Per Spec | 2.0 4.5 9.0 12.0 | 0.3 0.9 1.8 2.4 | 0.3 0.9 1.8 2.4 | 0.3 0.9 1.8 2.4 | V |
| I _{in} | Maximum Input Leakage Current ON/OFF Control Inputs | V _{in} = V _{CC} or GND | 12.0 | ± 0.1 | ± 1.0 | ± 1.0 | μА |
| Icc | Maximum Quiescent Supply Current (per Package) | $V_{in} = V_{CC}$ or GND $V_{IO} = 0$ V | 6.0 12.0 | 2 8 | 20 80 | 40 160 | μА |

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open. I/O pins must be connected to a properly terminated line or bus.

DC ELECTRICAL CHARACTERISTICS Analog Section (Voltages Referenced to GND)

| | | | | Gu | aranteed Li | mit | |
|------------------|--|---|----------------------------|----------------------|-----------------------|----------------------|------|
| Symbol | Parameter | Test Conditions | V _{CC} | – 55 to 25°C | ≤ 85 °C | ≤ 125°C | Unit |
| R _{on} | Maximum "ON" Resistance | $V_{in} = V_{IH}$ $V_{IS} = V_{CC}$ to GND $I_{S} \le 2.0$ mA (Figures 1, 2) | 2.0† 4.5 9.0 12.0 | — 170 85 85 | 215 106 106 | | Ω |
| | | $\begin{aligned} &V_{\text{in}} = V_{\text{IH}} \\ &V_{\text{IS}} = V_{\text{CC}} \text{ or GND (Endpoints)} \\ &I_{\text{S}} \leq 2.0 \text{ mA (Figures 1, 2)} \end{aligned}$ | 2.0 4.5 9.0 12.0 | — 85 63 63 | — 106 78 78 | — 130 95 95 | |
| ΔR _{on} | Maximum Difference in "ON" Resistance Between Any Two Channels in the Same Package | $\begin{aligned} &V_{\text{in}} = V_{\text{IH}} \\ &V_{\text{IS}} = 1/2 \left(V_{\text{CC}} - \text{GND} \right) \\ &I_{\text{S}} \leq 2.0 \text{ mA} \end{aligned}$ | 2.0 4.5 9.0 12.0 | — 30 20 20 | — 35 25 25 | 40 30 30 | Ω |
| I _{off} | Maximum Off–Channel Leakage Current, Any One Channel | $V_{\text{in}} = V_{\text{IL}}$ $V_{\text{IO}} = V_{\text{CC}}$ or GND Switch Off (Figure 3) | 12.0 | 0.1 | 0.5 | 1.0 | μА |
| I _{on} | Maximum On–Channel Leakage Current, Any One Channel | $V_{in} = V_{IH}$ $V_{IS} = V_{CC}$ or GND (Figure 4) | 12.0 | 0.1 | 0.5 | 1.0 | μА |

[†]At supply voltage (V_{CC} – GND) approaching 2 V the analog switch–on resistance becomes extremely non–linear. Therefore, for low–voltage operation, it is recommended that these devices only be used to control digital signals.

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, ON/OFF Control Inputs: $t_r = t_f = 6 \text{ ns}$)

| | | | Guaranteed Limit | | | |
|--|---|---------------------------|-----------------------|-----------------------------|-----------------------|------|
| Symbol | Parameter | V _{CC} | – 55 to 25°C | ≤ 85°C | ≤ 125°C | Unit |
| t _{PLH} , t _{PHL} | Maximum Propagation Delay, Analog Input to Analog Output (Figures 8 and 9) | 2.0 4.5 9.0 12.0 | 50 10 10 10 | 65 13 13 13 | 75 15 15 15 | ns |
| t _{PLZ} , t _{PHZ} | Maximum Propagation Delay, ON/OFF Control to Analog Output (Figures 10 and 11) | 2.0 4.5 9.0 12.0 | 150 30 30 30 | 190 38 30 30 | 225 45 30 30 | ns |
| t _{PZL} , t _{PZH} | Maximum Propagation Delay, ON/OFF Control to Analog Output (Figures 10 and 1 1) | | 125 25 25 25 | 160 32 32 32 32 | 185 37 37 37 | ns |
| С | Maximum Capacitance ON/OFF Control Input | _ | 10 | 10 | 10 | pF |
| | Control Input = GND Analog I/O Feedthrough | | 35 1.0 | 35 1.0 | 35 1.0 | |

| | | Typical @ 25°C, V _{CC} = 5.0 V | |
|----------|---|---|----|
| C_{PD} | Power Dissipation Capacitance (Per Switch) (Figure 13)* | 15 | pF |

ADDITIONAL APPLICATION CHARACTERISTICS (Voltages Referenced to GND Unless Noted)

| Symbol | Parameter | Test Conditions | v _{cc} | Limit* 25°C 54/74HC | Unit |
|--------|---|---|--------------------|---------------------------|------------------|
| BW | Maximum On–Channel Bandwidth or Minimum Frequency Response (Figure 5) | $\begin{aligned} f_{in} &= 1 \text{ MHz Sine Wave} \\ &\text{Adjust } f_{in} \text{ Voltage to Obtain 0 dBm at V}_{OS} \\ &\text{Increase } f_{in} \text{ Frequency Until dB Meter Reads} - 3 \text{ dB} \\ &R_L = 50 \ \Omega, \ C_L = 10 \text{ pF} \end{aligned}$ | 4.5 9.0 12.0 | 150 160 160 | MHz |
| _ | Off–Channel Feedthrough Isolation (Figure 6) | $ \begin{aligned} f_{in} &\equiv \text{Sine Wave} \\ \text{Adjust } f_{in} &\text{ Voltage to Obtain 0 dBm at V}_{IS} \\ f_{in} &= 10 \text{ kHz}, \text{ R}_{L} = 600 \ \Omega, \text{ C}_{L} = 50 \text{ pF} \end{aligned} $ | 4.5 9.0 12.0 | - 50 - 50 - 50 | dB |
| | | f_{in} = 1.0 MHz, R_L = 50 Ω , C_L = 10 pF | 4.5 9.0 12.0 | - 40 - 40 - 40 | |
| _ | Feedthrough Noise, Control to Switch (Figure 7) | $\begin{aligned} V_{in} & \leq 1 \text{ MHz Square Wave } (t_r = t_f = 6 \text{ ns}) \\ \text{Adjust } R_L \text{ at Setup so that } I_S = 0 \text{ A} \\ R_L = 600 \ \Omega, \ C_L = 50 \text{ pF} \end{aligned}$ | 4.5 9.0 12.0 | 60 130 200 | mV _{PP} |
| | | $R_L = 10 \text{ k}\Omega$, $C_L = 10 \text{ pF}$ | 4.5 9.0 12.0 | 30 65 100 | |
| _ | Crosstalk Between Any Two Switches (Figure 12) | $ \begin{aligned} f_{in} &\equiv \text{Sine Wave} \\ \text{Adjust } f_{in} &\text{ Voltage to Obtain 0 dBm at V}_{IS} \\ f_{in} &= 10 \text{ kHz}, \text{ R}_L = 600 \ \Omega, \text{ C}_L = 50 \text{ pF} \end{aligned} $ | 4.5 9.0 12.0 | - 70 - 70 - 70 | dB |
| | | f_{in} = 1.0 MHz, R_L = 50 Ω , C_L = 10 pF | 4.5 9.0 12.0 | - 80 - 80 - 80 | |
| THD | Total Harmonic Distortion (Figure 14) | $\begin{split} f_{in} = 1 \text{ kHz, } R_L = 10 \text{ k}\Omega \text{, } C_L = 50 \text{ pF} \\ \text{THD} = \text{THD}_{Measured} - \text{THD}_{Source} \\ V_{IS} = 4.0 \text{ V}_{PP} \text{ sine wave} \\ V_{IS} = 8.0 \text{ V}_{PP} \text{ sine wave} \\ V_{IS} = 11.0 \text{ V}_{PP} \text{ sine wave} \end{split}$ | 4.5 9.0 12.0 | 0.10 0.06 0.04 | % |

^{*} Guaranteed limits not tested. Determined by design and verified by qualification.

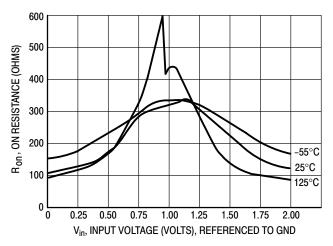


Figure 1a. Typical On Resistance, $V_{CC} = 2.0 \text{ V}$

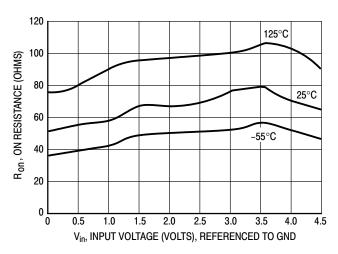


Figure 1b. Typical On Resistance, $V_{CC} = 4.5 \text{ V}$

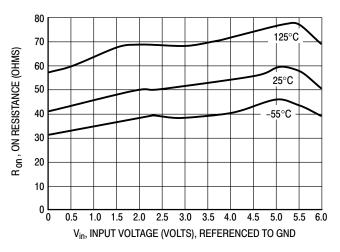


Figure 1c. Typical On Resistance, $V_{CC} = 6.0 \text{ V}$

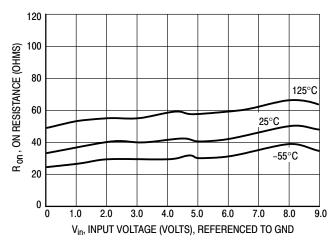


Figure 1d. Typical On Resistance, $V_{CC} = 9.0 \text{ V}$

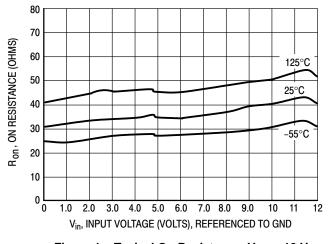


Figure 1e. Typical On Resistance, V_{CC} = 12 V

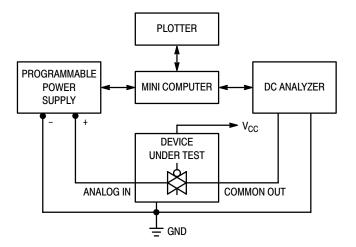


Figure 2. On Resistance Test Set-Up

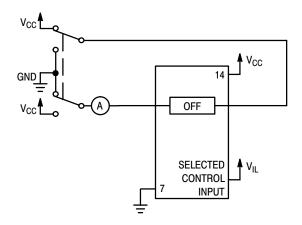


Figure 3. Maximum Off Channel Leakage Current, Any One Channel, Test Set-Up

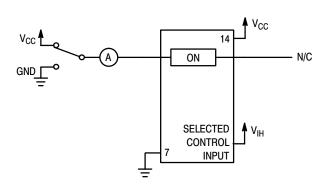
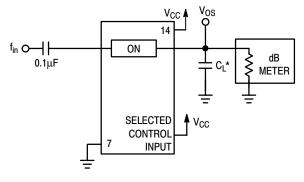
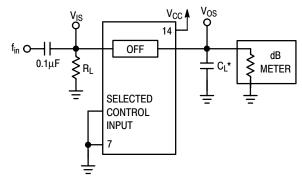


Figure 4. Maximum On Channel Leakage Current, Test Set-Up



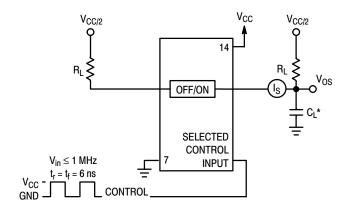
*Includes all probe and jig capacitance.

Figure 5. Maximum On-Channel Bandwidth
Test Set-Up



*Includes all probe and jig capacitance.

Figure 6. Off-Channel Feedthrough Isolation, Test Set-Up



*Includes all probe and jig capacitance.

Figure 7. Feedthrough Noise, ON/OFF Control to Analog Out, Test Set-Up

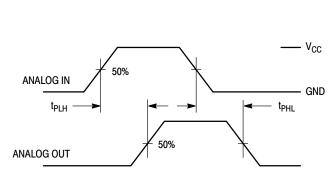
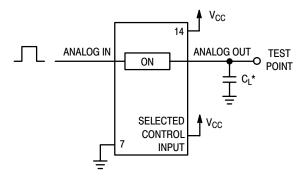
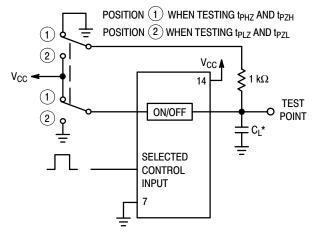


Figure 8. Propagation Delays, Analog In to Analog Out



^{*}Includes all probe and jig capacitance.

Figure 9. Propagation Delay Test Set-Up



^{*}Includes all probe and jig capacitance.

Figure 11. Propagation Delay Test Set-Up

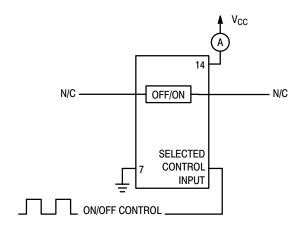


Figure 13. Power Dissipation Capacitance
Test Set-Up

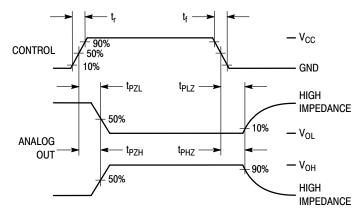
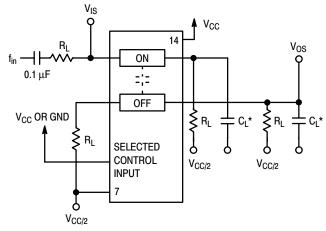
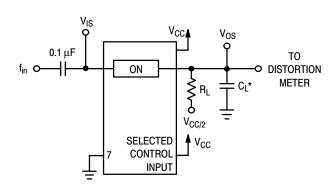


Figure 10. Propagation Delay, ON/OFF Control to Analog Out



*Includes all probe and jig capacitance.

Figure 12. Crosstalk Between Any Two Switches, Test Set-Up



*Includes all probe and jig capacitance.

Figure 14. Total Harmonic Distortion, Test Set-Up

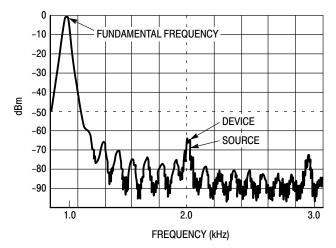


Figure 15. Plot, Harmonic Distortion

APPLICATION INFORMATION

The ON/OFF Control pins should be at V_{CC} or GND logic levels, V_{CC} being recognized as logic high and GND being recognized as a logic low. Unused analog inputs/outputs may be left floating (not connected). However, it is advisable to tie unused analog inputs and outputs to V_{CC} or GND through a low value resistor. This minimizes crosstalk and feedthrough noise that may be picked—up by the unused I/O pins.

The maximum analog voltage swings are determined by the supply voltages V_{CC} and GND. The positive peak analog voltage should not exceed V_{CC} . Similarly, the negative peak analog voltage should not go below GND. In the example

below, the difference between V_{CC} and GND is twelve volts. Therefore, using the configuration in Figure 16, a maximum analog signal of twelve volts peak-to-peak can be controlled.

When voltage transients above V_{CC} and/or below GND are anticipated on the analog channels, external diodes (Dx) are recommended as shown in Figure 17. These diodes should be small signal, fast turn—on types able to absorb the maximum anticipated current surges during clipping. An alternate method would be to replace the Dx diodes with MO•sorbs (high current surge protectors). MO•sorbs are fast turn—on devices ideally suited for precise DC protection with no inherent wear out mechanism.

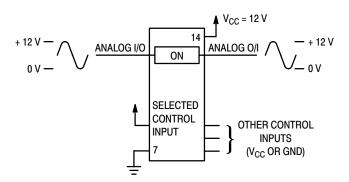


Figure 16. 12 V Application

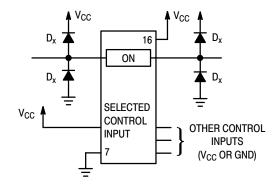


Figure 17. Transient Suppressor Application

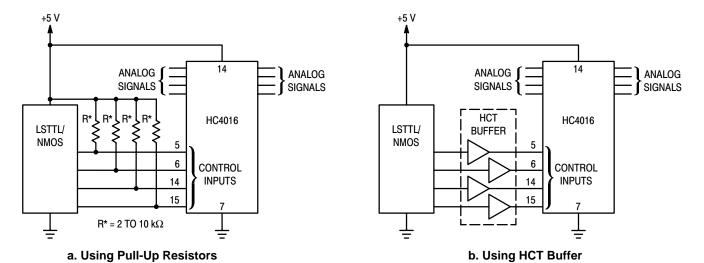


Figure 18. LSTTL/NMOS to HCMOS Interface

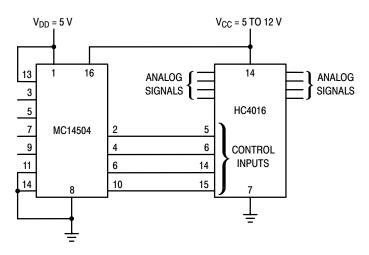


Figure 19. TTL/NMOS-to-CMOS Level Converter Analog Signal Peak-to-Peak Greater than 5 V (Also see HC4316)

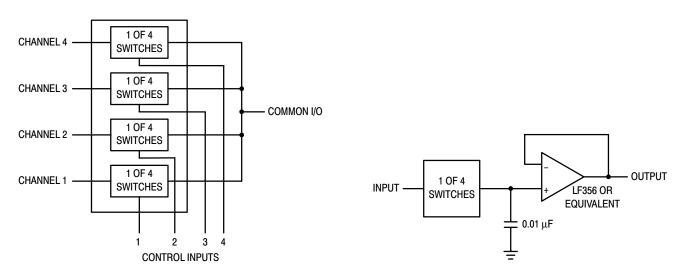


Figure 20. 4-Input Multiplexer

Figure 21. Sample/Hold Amplifier

OUTLINE DIMENSIONS

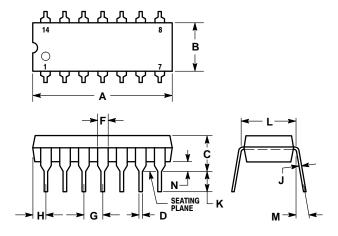
J SUFFIX CERAMIC DIP PACKAGE CASE 632-08 ISSUE Y -A--B-С -T-SEATING PLANE Κ **J** 14 PL

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
 4. DIMESNION F MAY NARROW TO 0.76 (0.030) WHERE THE LEAD ENTERS THE CERAMIC BODY.

| | INC | HES | MILLIN | IETERS |
|-----|-------|-------|----------|--------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 0.750 | 0.785 | 19.05 | 19.94 |
| В | 0.245 | 0.280 | 6.23 | 7.11 |
| С | 0.155 | 0.200 | 3.94 | 5.08 |
| D | 0.015 | 0.020 | 0.39 | 0.50 |
| F | 0.055 | 0.065 | 1.40 | 1.65 |
| G | 0.100 | BSC | 2.54 | BSC |
| J | 0.008 | 0.015 | 0.21 | 0.38 |
| K | 0.125 | 0.170 | 3.18 | 4.31 |
| L | 0.300 | BSC | 7.62 BSC | |
| М | 0° | 15° | 0° | 15° |
| N | 0.020 | 0.040 | 0.51 | 1.01 |

N SUFFIX PLASTIC DIP PACKAGE CASE 646-06 ISSUE L

⊕ 0.25 (0.010) M T B S



(0.010) (M) T A (S)

NOTES:

- NOTES:

 1. LEADS WITHIN 0.13 (0.005) RADIUS OF TRUE
 POSITION AT SEATING PLANE AT MAXIMUM
 MATERIAL CONDITION.

 2. DIMENSION L TO CENTER OF LEADS WHEN
 FORMED PARALLEL.

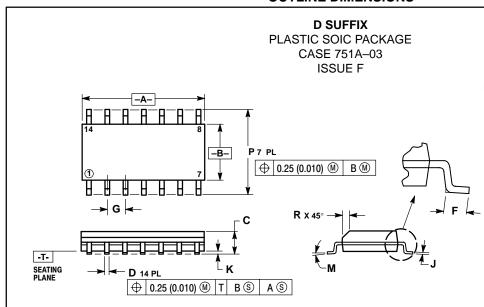
 3. DIMENSION B DOES NOT INCLUDE MOLD
 FLASH.

 4. POLYMOTE CONTINUE.

- 4. ROUNDED CORNERS OPTIONAL.

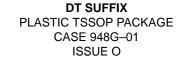
| | INC | HES | MILLIN | IETERS |
|-----|-----------|-------|----------|--------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 0.715 | 0.770 | 18.16 | 19.56 |
| В | 0.240 | 0.260 | 6.10 | 6.60 |
| С | 0.145 | 0.185 | 3.69 | 4.69 |
| D | 0.015 | 0.021 | 0.38 | 0.53 |
| F | 0.040 | 0.070 | 1.02 | 1.78 |
| G | 0.100 | BSC | 2.54 BSC | |
| Н | 0.052 | 0.095 | 1.32 | 2.41 |
| J | 0.008 | 0.015 | 0.20 | 0.38 |
| K | 0.115 | 0.135 | 2.92 | 3.43 |
| L | 0.300 BSC | | 7.62 | |
| M | 0° | 10° | 0° | 10° |
| N | 0.015 | 0.039 | 0.39 | 1.01 |

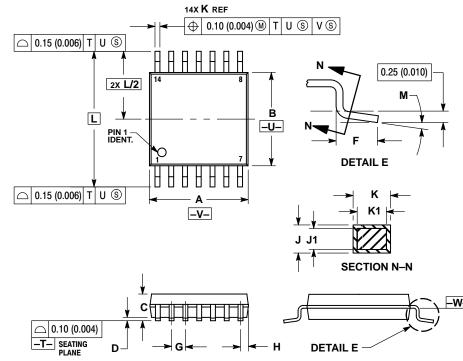
OUTLINE DIMENSIONS



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

| | MILLIM | ETERS | INC | HES | |
|-----|--------|-------|-----------|-------|--|
| DIM | MIN | MAX | MIN | MAX | |
| Α | 8.55 | 8.75 | 0.337 | 0.344 | |
| В | 3.80 | 4.00 | 0.150 | 0.157 | |
| С | 1.35 | 1.75 | 0.054 | 0.068 | |
| D | 0.35 | 0.49 | 0.014 | 0.019 | |
| F | 0.40 | 1.25 | 0.016 | 0.049 | |
| G | 1.27 | BSC | 0.050 BSC | | |
| J | 0.19 | 0.25 | 0.008 | 0.009 | |
| K | 0.10 | 0.25 | 0.004 | 0.009 | |
| M | 0° | 7° | 0° | 7° | |
| P | 5.80 | 6.20 | 0.228 | 0.244 | |
| R | 0.25 | 0.50 | 0.010 | 0.019 | |





NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE INTERLEAD
 FLASH OR PROTRUSION. INTERLEAD FLASH OR
 PROTRUSION SHALL NOT EXCEED
 0.25 (0.010) PER SIDE.
 DIMENSION K DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION. SHALL BE 0.08 (0.003) TOTAL IN
 EXCESS OF THE K DIMENSION AT MAXIMUM
 MATERIAL CONDITION.
 TERMINAL IN IMPRESS ARE SHOWN FOR
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

| | MILLIN | IETERS | INC | HES |
|-----|--------|--------|-----------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 4.90 | 5.10 | 0.193 | 0.200 |
| В | 4.30 | 4.50 | 0.169 | 0.177 |
| С | | 1.20 | | 0.047 |
| D | 0.05 | 0.15 | 0.002 | 0.006 |
| F | 0.50 | 0.75 | 0.020 | 0.030 |
| G | 0.65 | BSC | 0.026 BSC | |
| Н | 0.50 | 0.60 | 0.020 | 0.024 |
| J | 0.09 | 0.20 | 0.004 | 0.008 |
| J1 | 0.09 | 0.16 | 0.004 | 0.006 |
| K | 0.19 | 0.30 | 0.007 | 0.012 |
| K1 | 0.19 | 0.25 | 0.007 | 0.010 |
| L | 6.40 | | 0.252 | BSC |
| M | 0 ° | 8° | 0 ° | 8° |

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